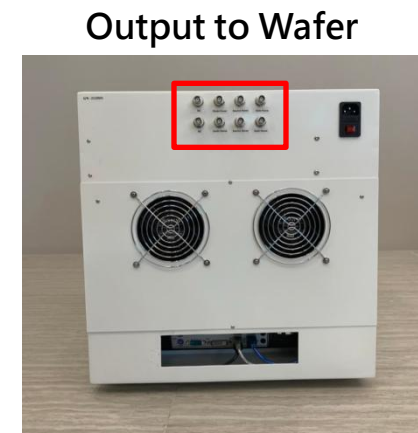
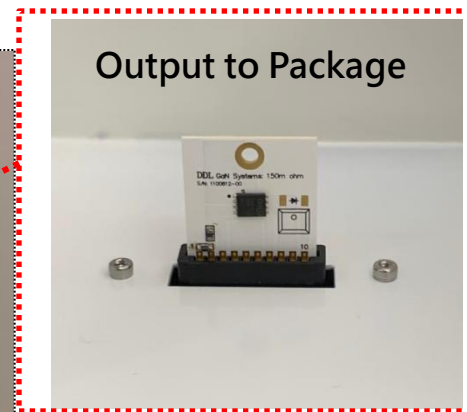
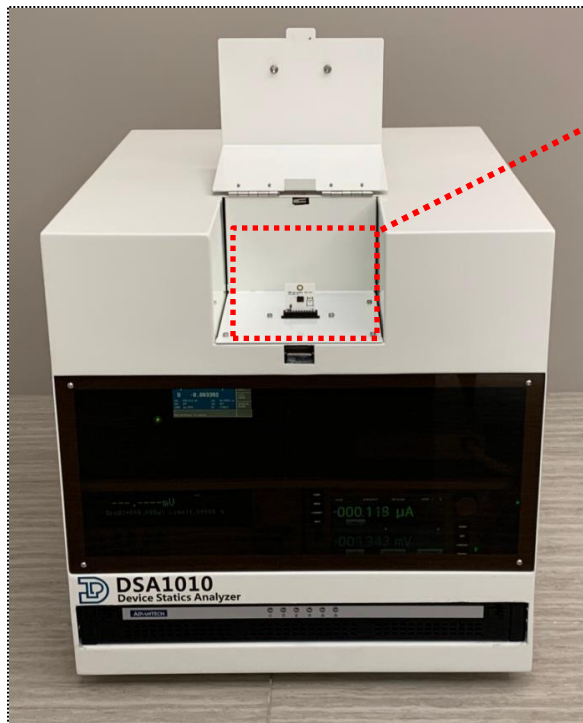


DSA1010 半導體靜態參數分析儀 (Device Statics Analyzer)

The DSA1010 Device Statics Analyzer can help developer to improve components, and it could also correctly evaluate the power loss and aging rate of components. Different from other power device analyzers, DSA1010 has a friendly operating interface, which can achieve intuitive use without programming, can measure and automatically adjust IV & CV at the same time, automatically switch between SMU and CMU modes, and has flexibility Features of the interface of the DUT.

主要技術規格
DC : 1000V/10mA, 40V/3A
Pulse : 20V/10A, 35V/5A
Friendly user interface - Transistor mode or Diode mode - Testing Plan for series tests
Flexible DUT connection - Package-Level - Wafer-Level
I-V & C-V automation - SMU + CMU auto switch - HV Bias-Tee integrated
DC & Pulse automation - DC SMU + Pulse SMU auto switch



DSA1010半導體靜態參數分析儀(Device Statics Analyzer)

Friendly user interface

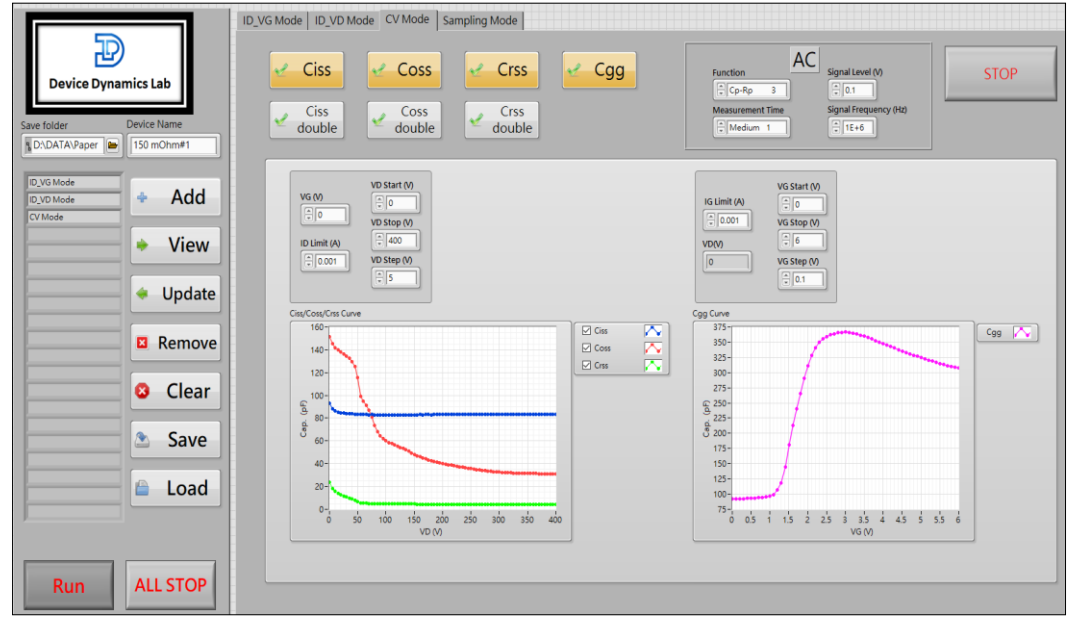


Figure of Merit (FOM) :

- Normalized to R_{dson} for size independent
- $R_{dson} * \text{Die size} = R_{sp}$ for wafer cost
- $R_{dson} * Q_{oss}$ for reverse (diode) switching loss
- $R_{dson} * Q_{gd}$ for turn-on speed (switching loss)
- $R_{dson} * E_{oss}$ for turn-off switching loss

FOM	Transphorm	GaN Systems	Infineon	Unit
R_{dson}	116	123	136	mΩ
Q_{oss}	36	18.9	15.7	nC
Q_{gd}	1.69	0.55	0.62	nC
E_{oss}	3.84	2.22	2.56	μJ
$R_{on} * Q_{oss}$	4176	2325	2135	mΩ * nC
$R_{on} * Q_{gd}$	196.0	67.7	84.3	mΩ * nC
$R_{on} * E_{oss}$	445.4	273.1	348.2	mΩ * μJ

